



GP800FSS12

Powerline N-Channel Single Switch IGBT Module

Preliminary Information

Replaces October 1999 version, DS5239-2.0

DS5239-3.0 January 2000

The GP800FSS12 is a single switch 1200V, robust n channel enhancement mode insulated gate bipolar transistor (IGBT) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion. The high impedance gate simplifies gate drive considerations enabling operation directly from low power control circuitry.

Fast switching times allow high frequency operation making the device suitable for the latest drive designs employing pwm and high frequency switching. The IGBT has a wide reverse bias safe operating area (RBSOA) for ultimate reliability in demanding applications.

These modules incorporate electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise earthed heat sinks for safety.

The powerline range of high power modules includes dual and single switch configurations with a range of current and voltage capabilities to match customer system demands.

Typical applications include dc motor drives, ac pwm drives, main traction drives and auxiliaries, large ups systems and resonant inverters.

FEATURES

- n - Channel
- Enhancement Mode
- High Input Impedance
- Optimised For High Power High Frequency Operation
- Isolated Base
- Full 1200V Capability
- 800A Per Module

APPLICATIONS

- High Power Switching
- Motor Control
- Inverters
- Traction Systems

KEY PARAMETERS

V_{CES}		1200V
$V_{CE(sat)}$	(typ)	2.7V
I_C	(max)	800A
$I_{C(PK)}$	(max)	1600A

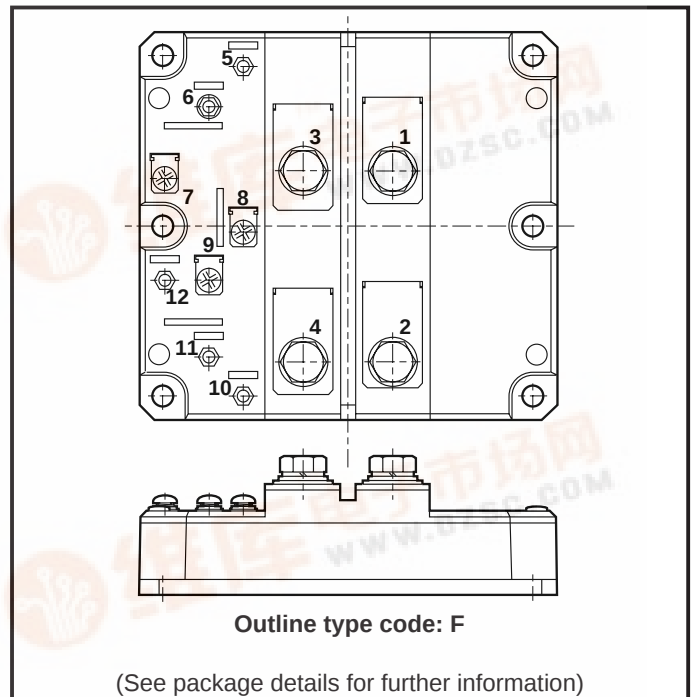


Fig. 1 Electrical connections - (not to scale)

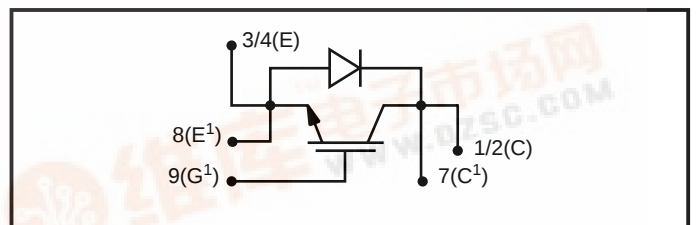


Fig.2 Single switch circuit diagram

ORDERING INFORMATION

Order As: **GP800FSS12**

Note: When ordering, please use the complete part number.



GP800FSS12

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	1200	V
V _{GES}	Gate-emitter voltage	-	±20	V
I _C	Collector current	DC, T _{case} = 25°C	1050	A
		DC, T _{case} = 75°C	800	A
		1ms, T _{case} = 75°C	1600	A
I _{C(PK)}				
P _{max}	Maximum power dissipation	T _{case} = 25°C (Transistor)	6000	W
V _{isol}	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Conditions	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - transistor	DC junction to case	-	21	°C/kW
R _{th(j-c)}	Thermal resistance - diode	DC junction to case -	-	40	°C/kW
R _{th(c-h)}	Thermal resistance - Case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	8	°C/kW
T _j	Junction temperature	Transistor	-	150	°C
		Diode	-	125	°C
T _{stg}	Storage temperature range	-	-40	125	°C
-	Screw torque	Mounting - M6	-	5	Nm
		Electrical connections - M4	-	2	Nm
		Electrical connections - M8	-	10	Nm

ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector cut-off current	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = V_{\text{CES}}$	-	-	1	mA
		$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = V_{\text{CES}}, T_{\text{case}} = 125^{\circ}\text{C}$	-	-	50	mA
I_{GES}	Gate leakage current	$V_{\text{GE}} = \pm 20\text{V}, V_{\text{CE}} = 0\text{V}$	-	-	± 4	μA
$V_{\text{GE(TH)}}$	Gate threshold voltage	$I_{\text{C}} = 120\text{mA}, V_{\text{GE}} = V_{\text{CE}}$	4	-	7.5	V
$V_{\text{CE(SAT)}}$	Collector-emitter saturation voltage	$V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 800\text{A}$	-	2.7	3.5	V
		$V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 800\text{A}, T_{\text{case}} = 125^{\circ}\text{C}$	-	3.2	4.0	V
I_{F}	Diode forward current	DC	-	-	800	A
I_{FM}	Diode maximum forward current	$t_{\text{p}} = 1\text{ms}$	-	-	1600	A
V_{F}	Diode forward voltage	$I_{\text{F}} = 800\text{A}$	-	2.2	2.4	V
		$I_{\text{F}} = 800\text{A}, T_{\text{case}} = 125^{\circ}\text{C}$	-	2.3	2.5	V
C_{ies}	Input capacitance	$V_{\text{CE}} = 25\text{V}, V_{\text{GE}} = 0\text{V}, f = 1\text{MHz}$	-	90	-	nF
L_{M}	Module inductance	-	-	20	-	nH

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INDUCTIVE SWITCHING CHARACTERISTICS

For definition of switching waveforms, refer to figure 3 and 4.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $R_{G(ON)} = R_{G(OFF)} = 3.3\Omega$ $L \sim 100nH$	-	1100	1300	ns
t_f	Fall time		-	150	200	ns
E_{OFF}	Turn-off energy loss		-	130	170	mJ
$t_{d(on)}$	Turn-on delay time		-	800	900	ns
t_r	Rise time		-	320	400	ns
E_{ON}	Turn-on energy loss		-	90	130	mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800A$ $V_R = 50\%V_{CES'}$ $dI_F/dt = 2000A/\mu s$	-	150	200	μC

T_{case} = 125°C unless stated otherwise.

$t_{d(off)}$	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $R_{G(ON)} = R_{G(OFF)} = 3.3\Omega$ $L \sim 100nH$	-	1300	1500	ns
t_f	Fall time		-	200	250	ns
E_{OFF}	Turn-off energy loss		-	170	250	mJ
$t_{d(on)}$	Turn-on delay time		-	950	1200	ns
t_r	Rise time		-	350	450	ns
E_{ON}	Turn-on energy loss		-	150	200	mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800A$ $V_R = 50\%V_{CES'}$ $dI_F/dt = 2000A/\mu s$	-	200	260	μC

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

SWITCHING DEFINITIONS

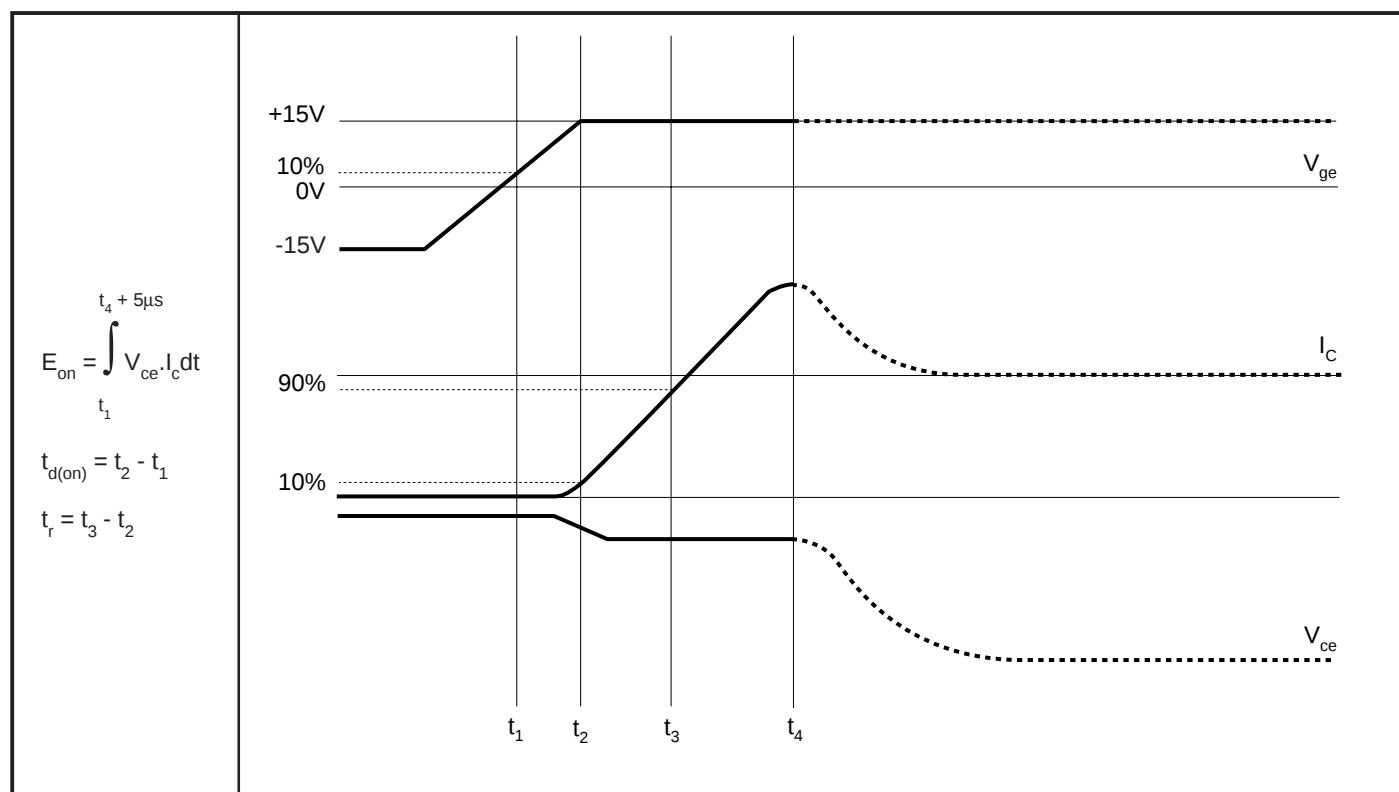


Fig.3 Definition of turn-on switching times

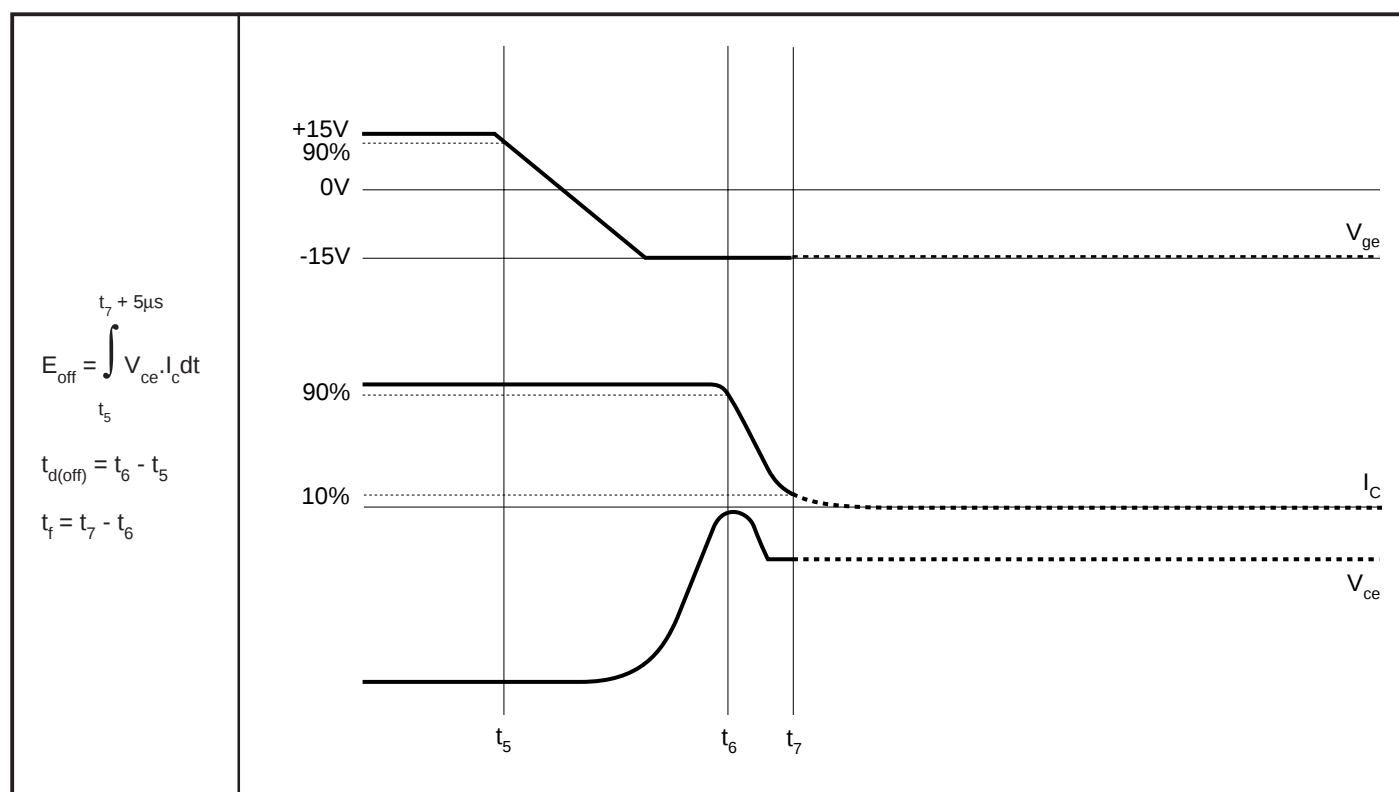


Fig.4 Definition of turn-off switching times

Caution: This device is sensitive to electrostatic discharge. Users should follow ESD handling procedures.

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CURVES

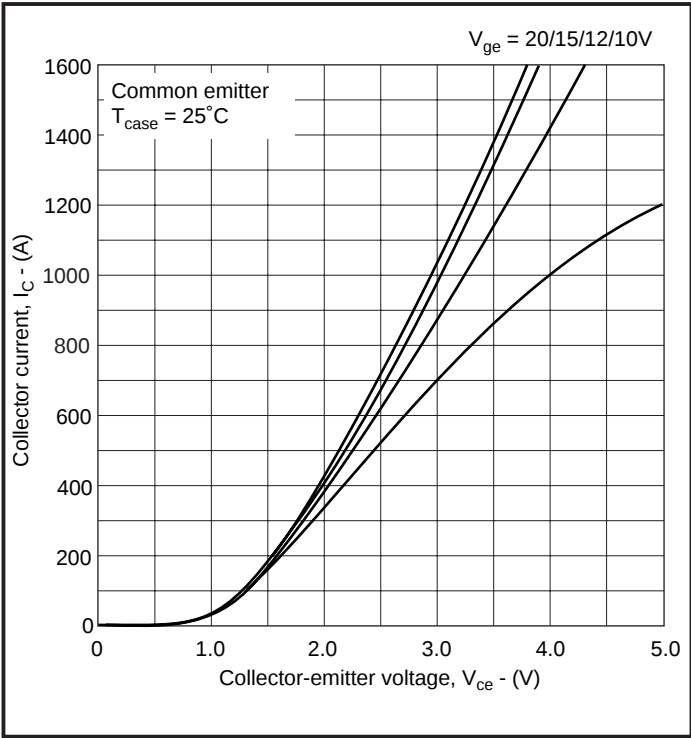


Fig.5 Typical output characteristics

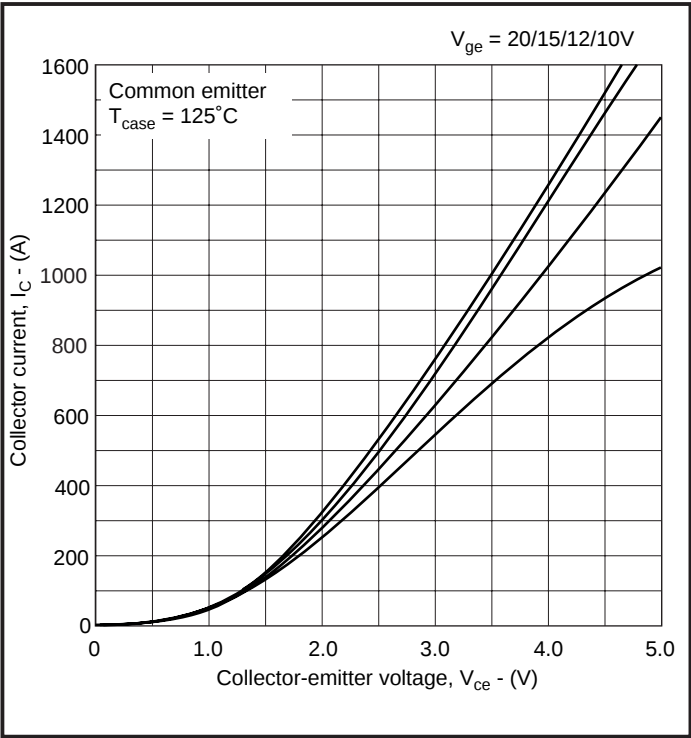


Fig.6 Typical output characteristics

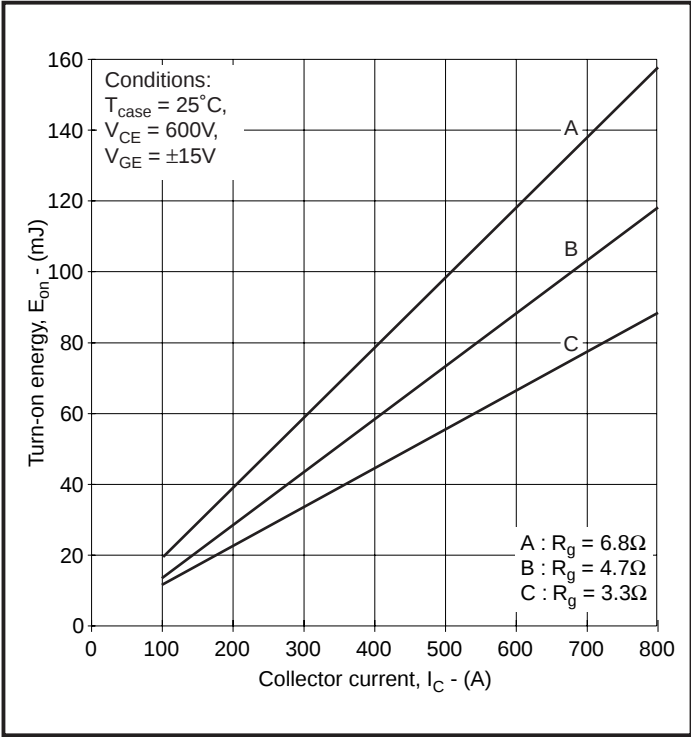


Fig.7 Typical turn-on energy vs collector current

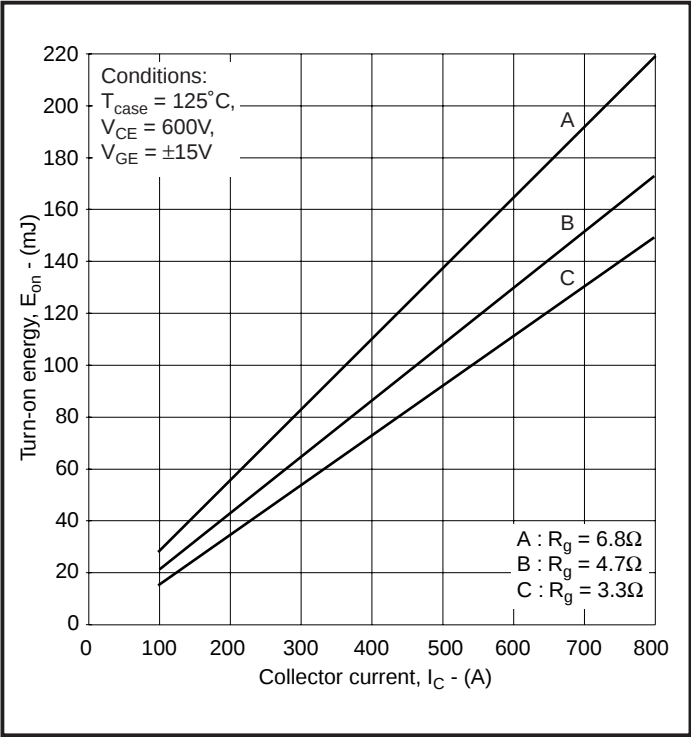


Fig.8 Typical turn-on energy vs collector current

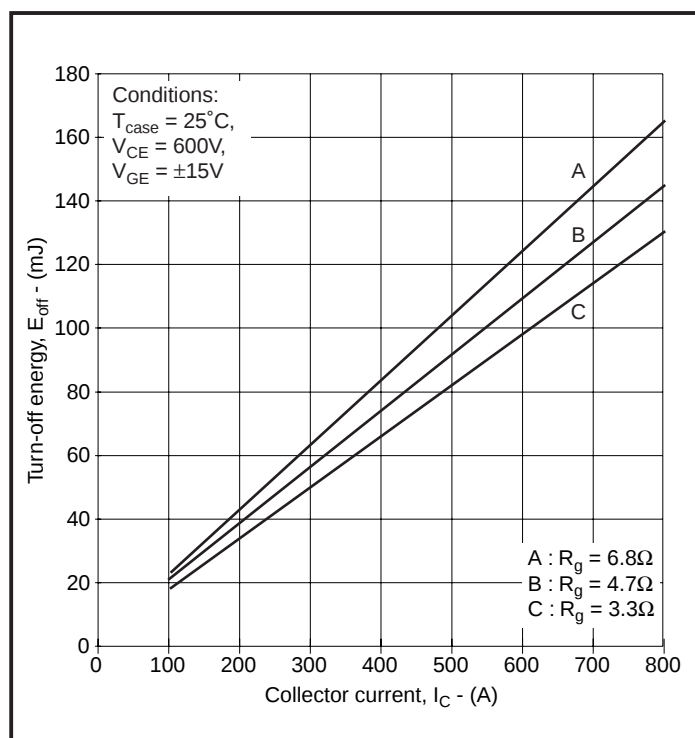


Fig.9 Typical turn-off energy vs collector current

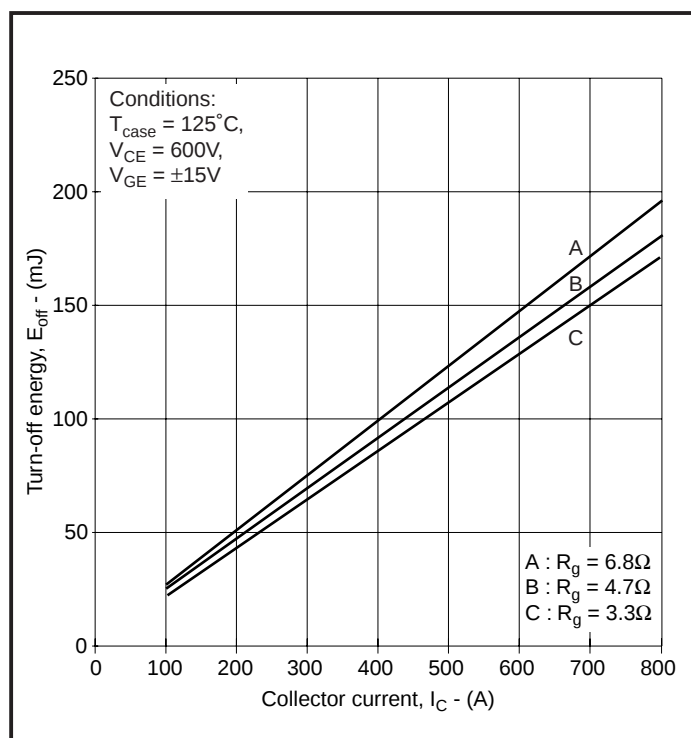


Fig.10 Typical turn-off energy vs collector current

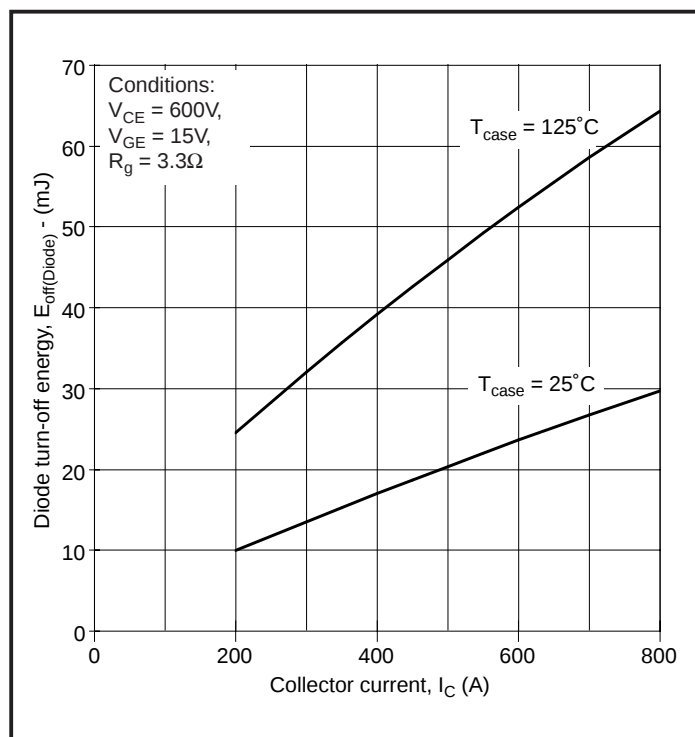


Fig.11 Typical diode reverse recovery charge vs collector current

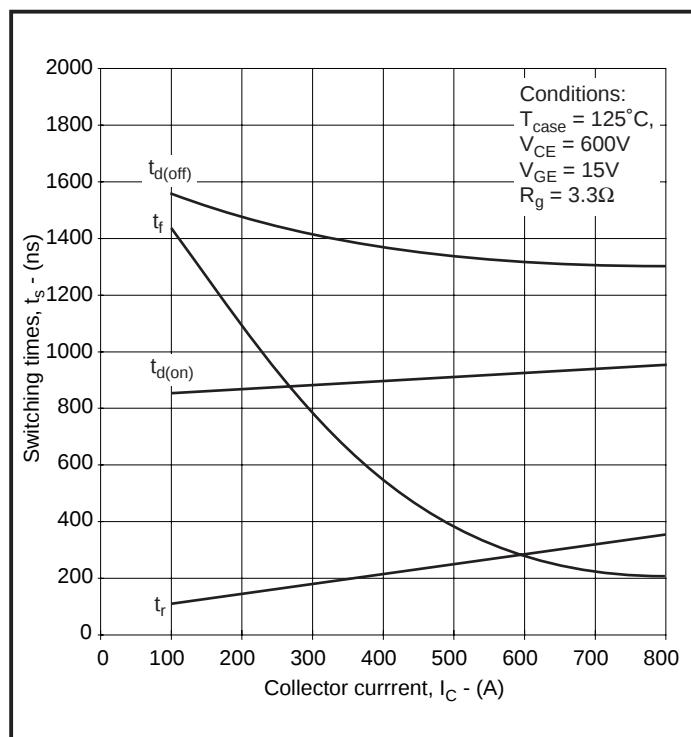


Fig.12 Typical switching characteristics

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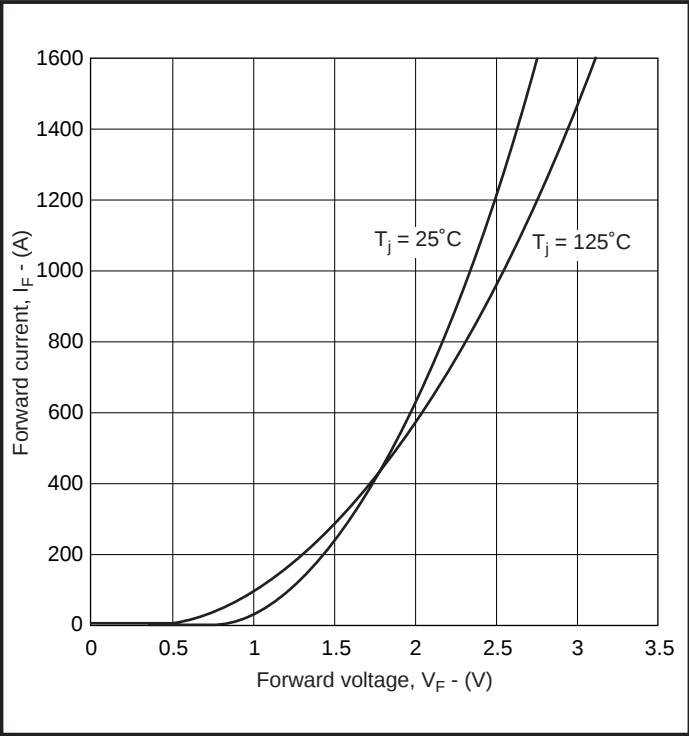


Fig.13 Diode typical forward characteristics

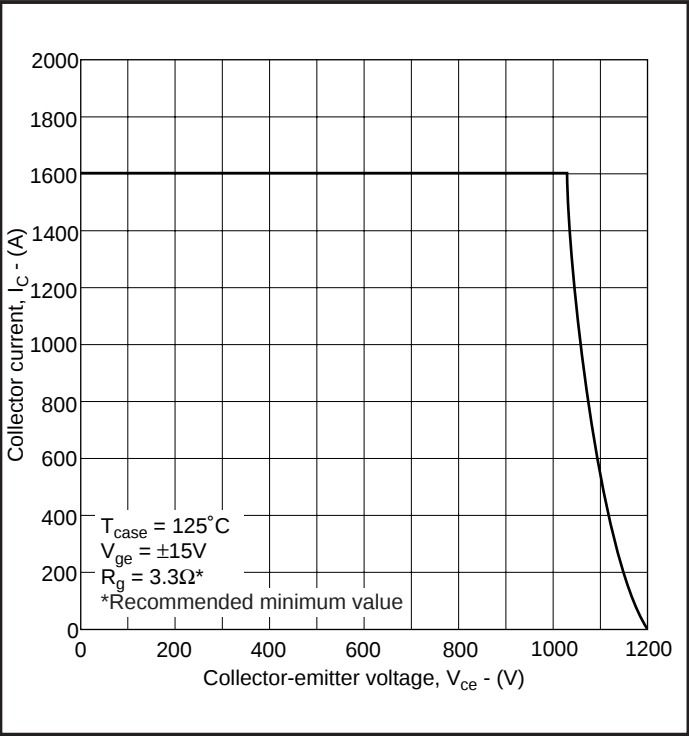


Fig.14 Reverse bias safe operating area

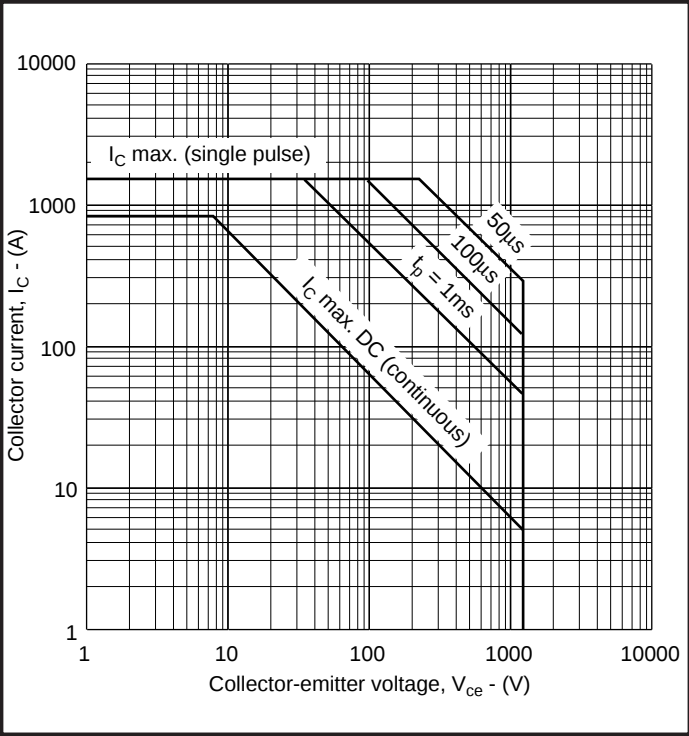


Fig.15 Forward bias safe operating area

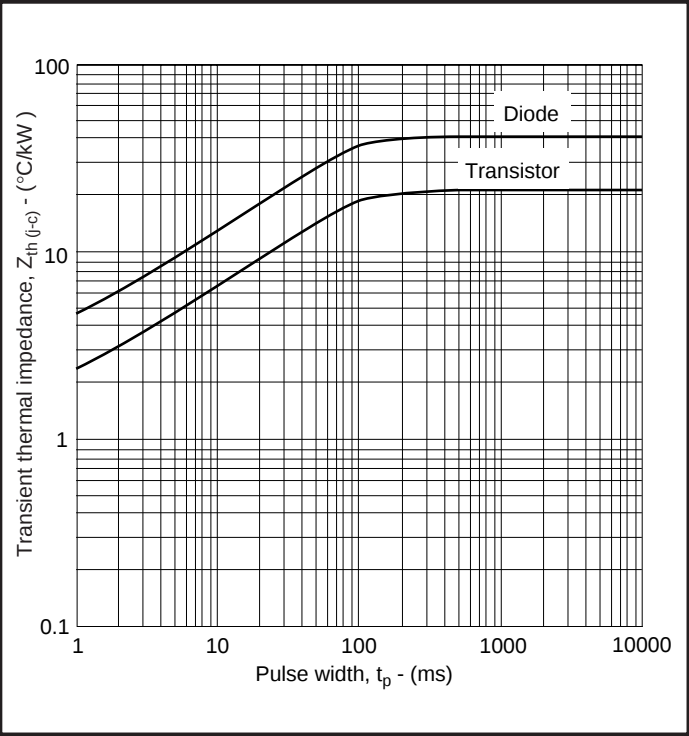


Fig.16 Transient thermal impedance

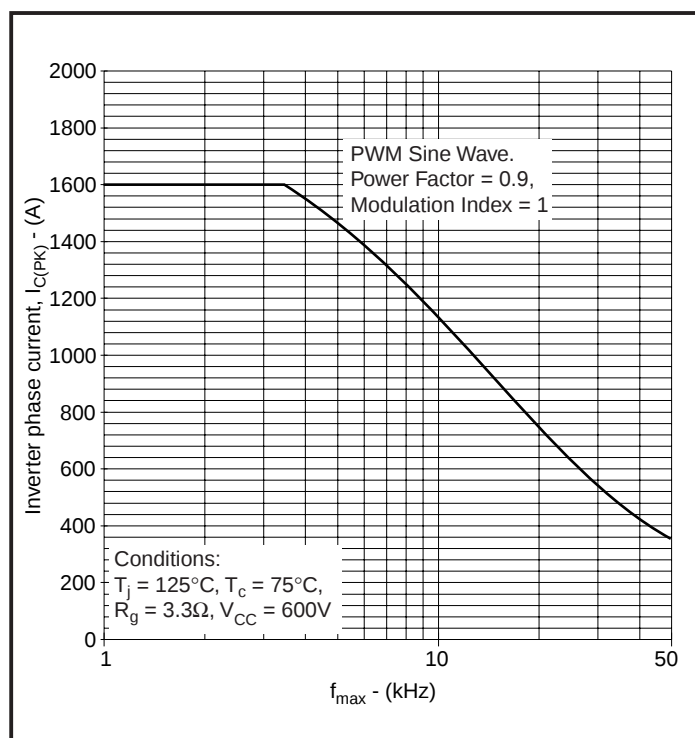


Fig.17 3-Phase inverter operating frequency

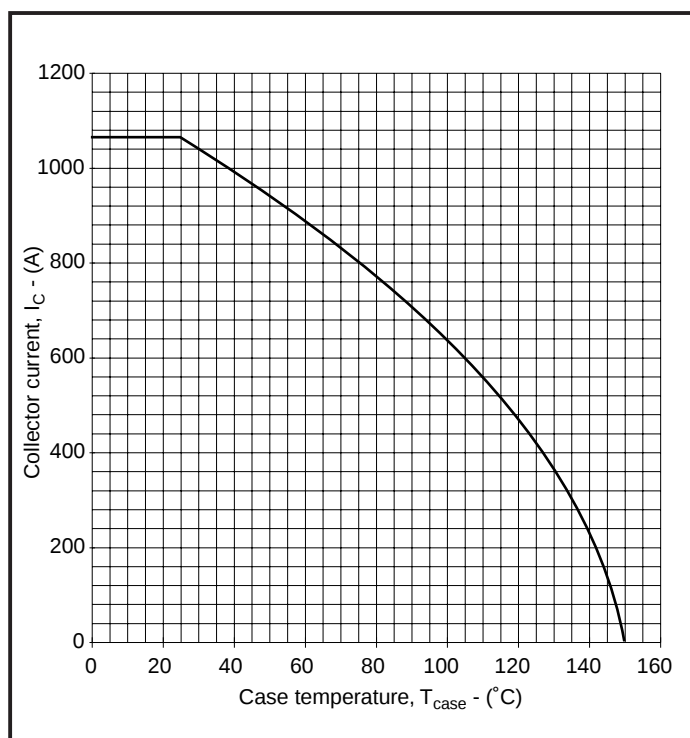
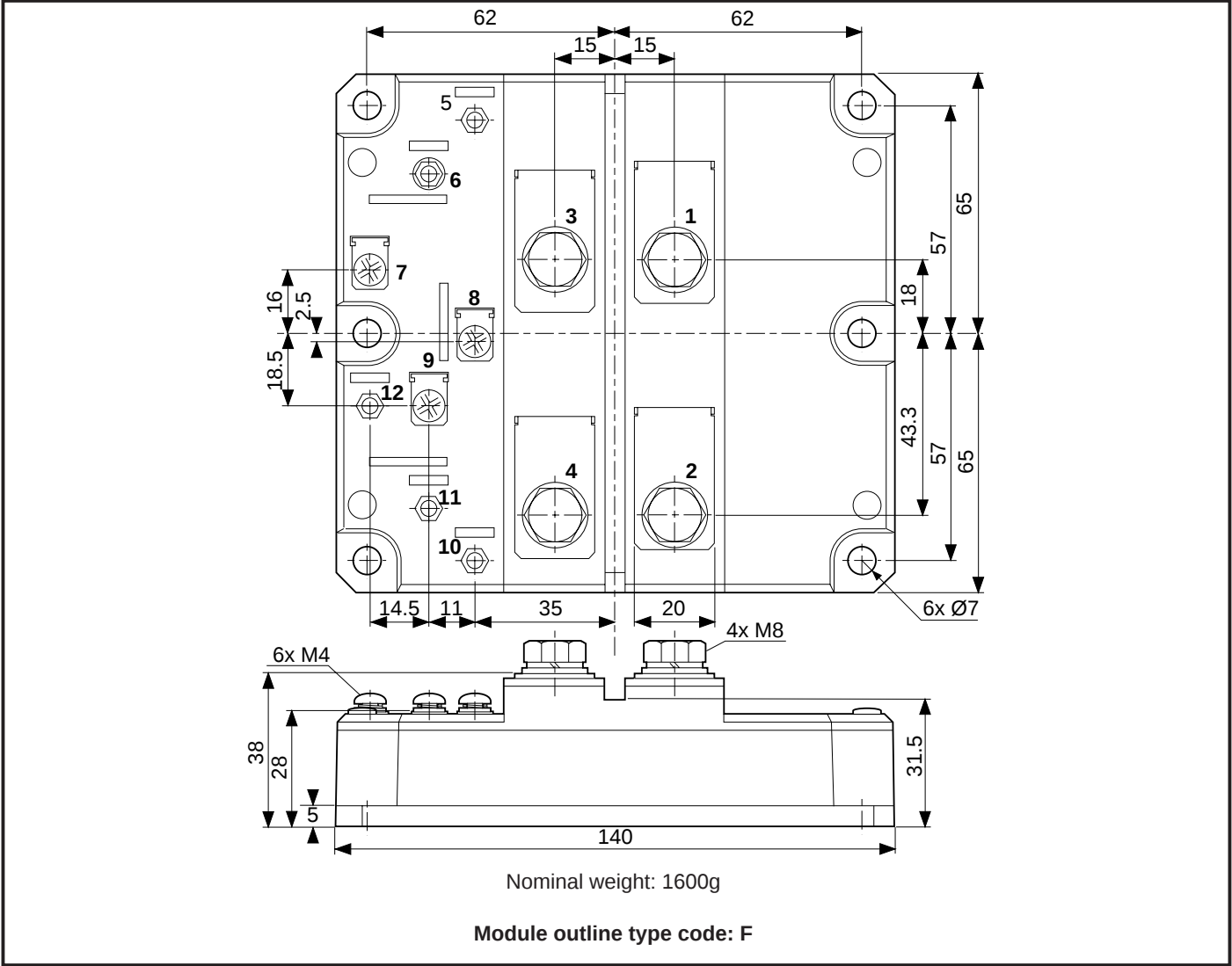


Fig.18 DC current rating vs case temperature

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Package Details

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



ASSOCIATED PUBLICATIONS

Title	Application Note
	Number
Electrostatic handling precautions	AN4502
An introduction to IGBTs	AN4503
IGBT ratings and characteristics	AN4504
Heatsink requirements for IGBT modules	AN4505
Calculating the junction temperature of power semiconductors	AN4506
Gate drive considerations to maximise IGBT efficiency	AN4507
Parallel operation of IGBTs – punch through vs non-punch through characteristics	AN4508
Guidance notes for formulating technical enquiries	AN4869
Principle of rating parallel connected IGBT modules	AN5000
Short circuit withstand capability in IGBTs	AN5167
Driving high power IGBTs with concept gate drivers	AN5190

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The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

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Power Assembly has it's own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or the factory.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

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